

AMENDMENTS TO THE CLAIMS

1-26. (Canceled).

27. (Currently amended) An array of resistance variable memory cells comprising:

at least one pillar of stacked material layers on a semiconductor substrate, the stacked layers comprising a first electrode, a chalcogenide glass material layer having metal ions diffused therein in contact with the first electrode and being capable of changing resistance under the influence of an applied voltage, a metal material layer in contact with the chalcogenide glass material layer, and a second electrode in contact with the metal material layer, the at least one pillar not located within a via.

28-48. (Canceled).

49. (Previously presented) The array of Claim 27, wherein the metal ions comprise silver ions.

50. (Previously presented) The array of Claim 27, wherein at least one of the first and second electrodes is tungsten.

51. (Currently amended) The array of Claim 27, wherein the metal material layer comprises silver.